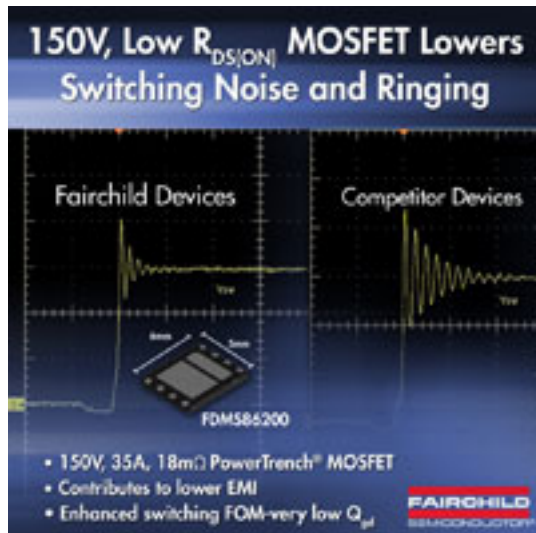


MOSFET Increases Efficiency and Output Power in LED Lighting, Solar and Industrial Designs



Leveraging its advanced process and packaging technologies, as well as system expertise, Fairchild Semiconductor has released a 150V MOSFET with low $R_{DS(ON)}$ (17 mΩ MAX) and an optimized Figure of Merit (FOM) (17 mΩ * 33nC² Max) to bring high efficiency, lower power dissipation and less heat in a 5 mm x 6 mm MLP footprint.

The FDMS86200 is designed using shielded-gate MOSFET technology that brings lower switching noise and ringing to the design, contributing to lower EMI. Without this proprietary technology feature, a designer would be forced to choose a 200V MOSFET, which would double the $R_{DS(ON)}$ and lower the overall efficiency.

Fairchild's FDMS86200 also features an improved body diode that boosts switching performance by reducing losses. This unique combination of functional, process and packaging innovation and overall system expertise enables greater innovation for electronic manufacturers.

Fairchild's MOSFET portfolio has a wide range of breakdown voltages (20V to 1000V) and advanced packaging technologies ranging from 1 mm x 1.5 mm WL-CSP to 20 mm x 26 mm TO264 packaging.

Source URL (retrieved on 01/30/2015 - 7:52pm):

http://www.wirelessdesignmag.com/product-releases/2010/08/mosfet-increases-efficiency-and-output-power-led-lighting-solar-and-industrial-designs?qt-digital_editions=0